Doping of Self-Catalyzed Nanowires under the Influence of Droplets

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Supporting information 1:

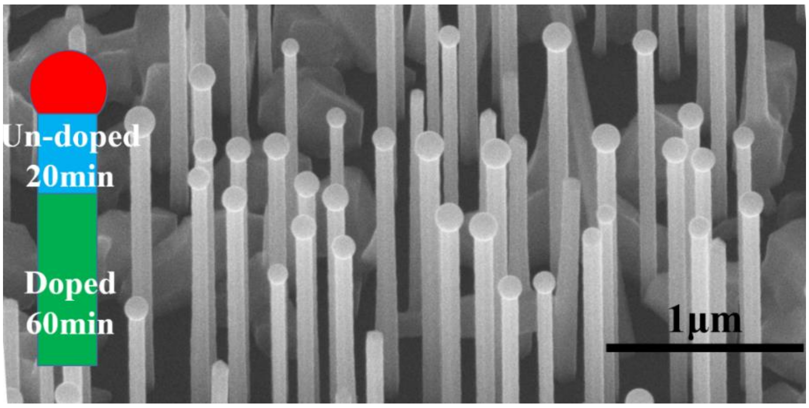

Figure S1. SEM image of GaAs NWs grown with a 60 mins Be doped duration (nominal concentration $1.6\times10^{18}/cm^3$) and then followed by a 20 mins non-doped duration. The Ga droplet is on the exact top of the NW.

Supporting information 2:

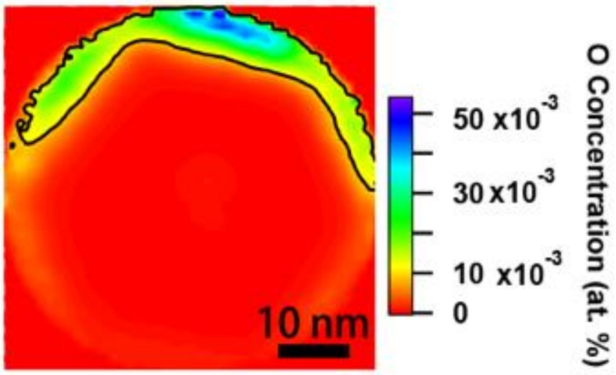

Figure S2. Oxygen distribution map in the NW cross-section shown in Figure 3a.